

Figure 1. Pin Assignment

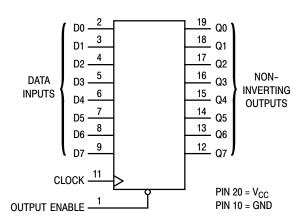


Figure 2. Logic Diagram

Design Criteria	Value	Units
Internal Gate Count*	71.5	ea
Internal Gate Propagation Delay	1.5	ns
Internal Gate Power Dissipation	5.0	μW
Speed Power Product	0.0075	рЈ

^{*}Equivalent to a two-input NAND gate.

FUNCTION TABLE

	Output		
OE	Clock	D	Q
L	7	Н	Н
L		L	L
L	L,H, ∕_	X	No Change
Н	X	Х	Z

X = don't careZ = high impedance

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74HCT574AN	PDIP-20	18 Units / Box
MC74HCT574ANG	PDIP-20 (Pb-Free)	18 Units / Box
MC74HCT574ADW	SOIC-20 WIDE	38 Units / Rail
MC74HCT574ADWG	SOIC-20 WIDE (Pb-Free)	38 Units / Rail
MC74HCT574ADWR2	SOIC-20 WIDE	1000 Tape & Reel
MC74HCT574ADWR2G	SOIC-20 WIDE (Pb-Free)	1000 Tape & Reel
MC74HCT574ADTR2	TSSOP-20*	2500 Tape & Reel
MC74HCT574ADTR2G	TSSOP-20*	2500 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}This package is inherently Pb-Free.

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	-0.5 to $V_{CC} + 0.5$	V
V _{out}	DC Output Voltage (Referenced to GND)	- 0.5 to V _{CC} + 0.5	V
I _{in}	DC Input Current, per Pin	± 20	mA
I _{out}	DC Output Current, per Pin	± 35	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	± 75	mA
P _D	Power Dissipation in Still Air, Plastic DIP† SOIC Package†	750 500	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 secs (Plastic DIP or SOIC Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, Vin and Vout should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC}.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

†Derating – Plastic DIP: –10 mW/°C from 65° to 125°C – SOIC Package: –7 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	4.5	5.5	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V _{CC}	V
T _A	Operating Temperature, All Package Types		+ 125	°C
t _r , t _f	Input Rise and Fall Time (Figure 3)	0	500	ns

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu	Guaranteed Limit		
Symbol	Parameter	Test Conditions	V _{CC}	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
V _{IH}	Minimum High-Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$	4.5 5.5	2.0 2.0	2.0 2.0	2.0 2.0	V
V _{IL}	Maximum Low-Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out} \le 20 \mu\text{A}$	4.5 5.5	0.8 0.8	0.8 0.8	0.8 0.8	V
V _{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \ \mu A$	4.5 5.5	4.4 5.4	4.4 5.4	4.4 5.4	
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 6.0 \text{ mA}$	4.5	3.98	3.84	3.7	V
V _{OL}	Maximum Low-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \ \mu\text{A}$	4.5 5.5	0.1 0.1	0.1 0.1	0.1 0.1	
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 6.0 \text{ mA}$	4.5	0.26	0.33	0.4	
I _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	5.5	± 0.1	± 1.0	± 1.0	μΑ
I _{CC}	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	5.5	4.0	40	160	μΑ
I _{OZ}	Maximum Three–State Leakage Current	$V_{in} = V_{IL} \text{ or } V_{IH} \text{ (Note 1)}$ $V_{out} = V_{CC} \text{ or GND}$	5.5	- 0.5	- 5.0	- 10	μΑ
ΔI_{CC}	Additional Quiescent Supply Current	V _{in} = 2.4 V, Any One Input V _{in} = V _{CC} or GND, Other Inputs		≥ - 55 °C	25°C to	125°C	
		$I_{\text{out}} = 0 \mu\text{A}$	5.5	2.9	2	.4	mA

^{1.} Output in high-impedance state.

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

AC ELECTRICAL CHARACTERISTICS (V_{CC} = $5.0 \text{ V} \pm 10\%$, C_L = 50 pF, Input t_r = t_f = 6.0 ns)

		Guaranteed Limit			
Symbol	Parameter	– 55 to 25°C	≤ 85 °C	≤ 125°C	Unit
f _{MAX}	Maximum Clock Frequency (50% Duty Cycle) (Figures 3 and 6)	30	24	20	MHz
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Clock to Q (Figures 3 and 6)	30	38	45	ns
t _{PLZ} , t _{PHZ}	Maximum Propagation Delay, Output Enable to Q (Figures 4 and 7)	28	35	42	ns
t _{PZH} , t _{PZL}	Maximum Propagation Delay Time, Output Enable to Q (Figures 4 and 7)	28	35	42	ns
t _{TLH} ,	Maximum Output Transition Time, Any Output (Figures 3, 4 and 6)	12	15	18	ns
t _{THL}					
C _{in}	Maximum Input Capacitance	10	10	10	pF

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

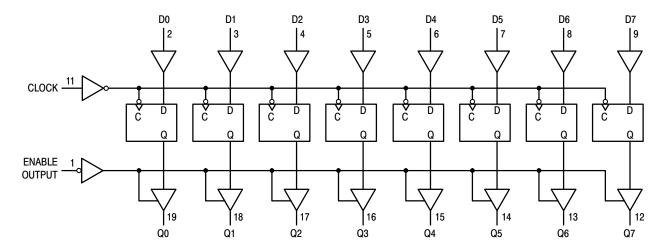
		Typical @ 25°C, V _{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Per Flip-Flop)*	58	pF

^{*} Used to determine the no–load dynamic power consumption: $P_D = C_{PD} \ V_{CC}^2 f + I_{CC} \ V_{CC}$. For load considerations, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

TIMING REQUIREMENTS (V_{CC} = 5.0 V \pm 10%, C_L = 50 pF, Input t_f = t_f = 6.0 ns)

			Guaranteed Limit						
			– 55 to	25°C	≤ 8	5°C	≤ 12	25°C	
Symbol	Parameter	Figure	Min	Max	Min	Max	Min	Max	Unit
t _{su}	Minimum Setup Time, Data to Clock	5	10		13		15		ns
t _h	Minimum Hold Time, Clock to Data	5	5.0		5.0		5.0		ns
t _w	Minimum Pulse Width, Clock	3	15		19		22		ns
t _r , If	Maximum Input Rise and Fall Times	3		500		500		500	ns

EXPANDED LOGIC DIAGRAM



SWITCHING WAVEFORMS

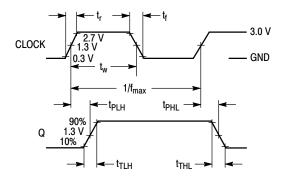


Figure 3.

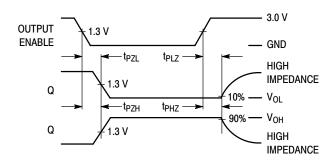


Figure 4.

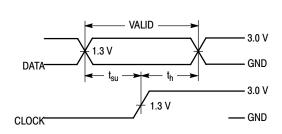
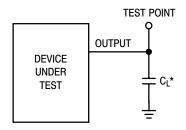


Figure 5.



*Includes all probe and jig capacitance

Figure 6. Test Circuit

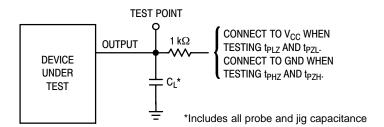
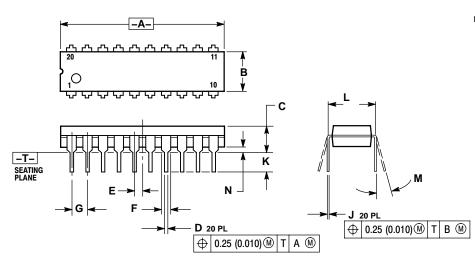


Figure 7. Test Circuit

PACKAGE DIMENSIONS

PDIP-20 **N SUFFIX** PLASTIC DIP PACKAGE CASE 738-03 ISSUE E

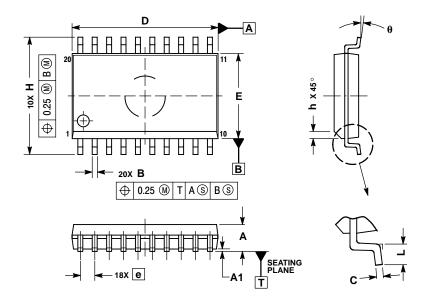


NOTES:

- (OTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH. 3. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL. 4. DIMENSION B DOES NOT INCLUDE MOLD
- FLASH.

	INC	HES	MILLIN	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	1.010	1.070	25.66	27.17	
В	0.240	0.260	6.10	6.60	
С	0.150	0.180	3.81	4.57	
D	0.015	0.022	0.39	0.55	
E	0.050	BSC	1.27 BSC		
F	0.050	0.070	1.27	1.77	
G	0.100	BSC	2.54 BSC		
J	0.008	0.015	0.21	0.38	
K	0.110	0.140	2.80	3.55	
L	0.300 BSC		7.62	BSC	
M	0°	15°	0°	15°	
N	0.020	0.040	0.51	1.01	

SOIC-20 **DW SUFFIX** CASE 751D-05 ISSUE G



NOTES:

- NOTES:

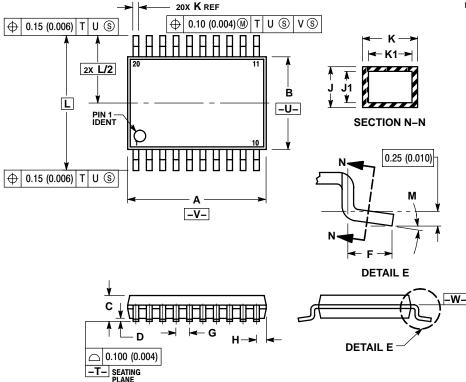
 1. DIMENSIONS ARE IN MILLIMETERS.
 2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
 5. DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS				
DIM	MIN	MAX			
Α	2.35	2.65			
A1	0.10	0.25			
В	0.35	0.49			
С	0.23	0.32			
D	12.65	12.95			
E	7.40	7.60			
е	1.27	BSC			
Н	10.05	10.55			
h	0.25	0.75			
L	0.50	0.90			
A	0 °	7 °			

PACKAGE DIMENSIONS

TSSOP-20 DT SUFFIX 20 PIN PLASTIC TSSOP PACKAGE CASE 948E-02

ISSUE B



NOTES:

SIDE

- DIMENSIONING AND TOLERANCING
- PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION:
- MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE
 MOLD FLASH, PROTRUSIONS OR GATE
 BURRS. MOLD FLASH OR GATE BURRS
 SHALL NOT EXCEED 0.15 (0.006) PER
- DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE
 DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	6.40	6.60	0.252	0.260
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026	BSC
Н	0.27	0.37	0.011	0.015
_	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K 1	0.19	0.25	0.007	0.010
L	6.40	BSC	0.252	BSC
M	0°	8°	0°	8°

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